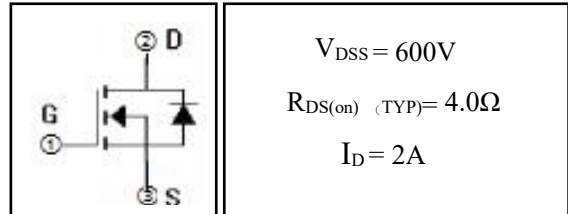


## 2A 600V N-channel Enhancement Mode Power MOSFET

### 1 Description

These N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. Which accords with the RoHS standard.



### 2 Features

- Fast Switching
- Low ON Resistance( $R_{dson} \leq 4.5\Omega$ )
- Low Gate Charge(Typ:8nC)
- Low Reverse Transfer Capacitances(Typ:3.8pF)
- 100% Single Pulse Avalanche Energy Test
- 100%  $\Delta V_{DS}$  Test

### 3 Applications

- used in various power switching circuit for system miniaturization and higher efficiency.
- Power switch circuit of electron ballast and adaptor.



### 4 Electrical Characteristics

#### 4.1 Absolute Maximum Rating( $T_c=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Value		Units	
		2N60/I2N60/E2N60 /B2N60/D2N60	F2N60		
Drain-Source Voltage	$V_{DS}$	600		V	
Gate-Drain Voltage	$V_{GS}$	$\pm 30$		V	
Drain Current(continuous)	$I_D (T=25^\circ C)$ $(T=100^\circ C)$	2		A	
		1.26		A	
Drain Current(Pulsed) <sup>(Note 1)</sup>	$I_{DM}$	8		A	
Single Pulse Avalanche Energy <sup>(Note 5)</sup>	$E_{AS}$	64		mJ	
Avalanche Energy Repetitive <sup>(Note 1)</sup>	$E_{AR}$	6.4		mJ	
Avalanche Current <sup>(Note 1)</sup>	$I_{AR}$	3.6		A	
Peak Diode Recovery $dv/dt$ <sup>(Note 6)</sup>	$dv/dt$	5		V/ns	
Total Dissipation	$T_a=25^\circ C$	$P_{tot}$	2	2	W
	$T_c=25^\circ C$	$P_{tot}$	35	20	W
Junction Temperature	$T_j$	150		$^\circ C$	
storage Temperature	$T_{stg}$	-55~150		$^\circ C$	
Maximum Temperature for soldering	$T_L$	300		$^\circ C$	

#### 4.2 Thermal Characteristics

Parameter	Symbol	Value		Units
		2N60/I2N60/E2N60 /B2N60/D2N60	F2N60	
Thermal Resistance Junction to Case-sink	$R_{thJC}$	3.57	6.25	$^\circ C/W$
Thermal Resistance Junction to Ambient	$R_{thJA}$	62.5	62.5	$^\circ C/W$

### 4.3 Electrical Characteristics (T<sub>c</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Units
			min	typ	max	
<b>Off Characteristics</b>						
Drain-source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	600	--	--	V
Drain-to-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V, T <sub>C</sub> =25 °C	--	--	1	μA
		V <sub>DS</sub> =480V, V <sub>GS</sub> =0V, T <sub>C</sub> =125 °C	--	--	100	μA
Gate-to-Source Forward Leakage	I <sub>GSSF</sub>	V <sub>GS</sub> =+30V	--	--	100	nA
Gate-to-Source Reverse Leakage	I <sub>GSSR</sub>	V <sub>GS</sub> =-30V	--	--	-100	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2	--	4	V
Drain-source on Resistance	R <sub>DSON</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1A	--	4	4.5	Ω
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Forward Transfer conductance	g <sub>fs</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =1A	2	--	--	S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz	--	280	--	pF
Output Capacitance	C <sub>oss</sub>		--	30	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	3.8	--	
<b>Switching Characteristics</b> <sup>(note4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> =2A, V <sub>DD</sub> =300V, V <sub>GS</sub> =10V, R <sub>G</sub> =18Ω	--	7.8	--	nS
Turn-on Rise Time	t <sub>r</sub>		--	5.5	--	nS
Turn-off Delay Time	t <sub>d(off)</sub>		--	33	--	nS
Turn-off Fall Time	t <sub>f</sub>		--	16	--	nS
Total Gate Charge	Q <sub>g</sub>	I <sub>D</sub> =2A, V <sub>DD</sub> =480V, V <sub>GS</sub> =10V	--	8.5	--	nC
Gate-to-Source Charge	Q <sub>gs</sub>		--	1.5	--	
Gate-to-Drain("Miller") Charge	Q <sub>gd</sub>		--	4	--	
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>FSD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =2A	--	--	1.5	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		--	--	2	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> =25 °C, I <sub>F</sub> =2A, dI <sub>F</sub> /dt=100A/μS, V <sub>GS</sub> =0V	--	80	--	nS
Reverse Recovery Charge	Q <sub>rr</sub>		--	180	--	nC
Reverse Recovery Current	I <sub>RRM</sub>		--	4.5	--	A

**Notes:**

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, t<sub>s</sub>≤10sec.
- 3: Pulse width ≤ 300μs, duty cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production.
5. L=10mH, I<sub>D</sub>=3.58A, V<sub>DD</sub>=50V, V<sub>GATE</sub>=600V, Start T<sub>J</sub>=25 °C.
6. I<sub>SD</sub>=2A, di/dt≤100A/μs, V<sub>DD</sub>≤BV<sub>DSS</sub>, Start T<sub>J</sub>=25 °C.

**5 Typical characteristics diagrams**

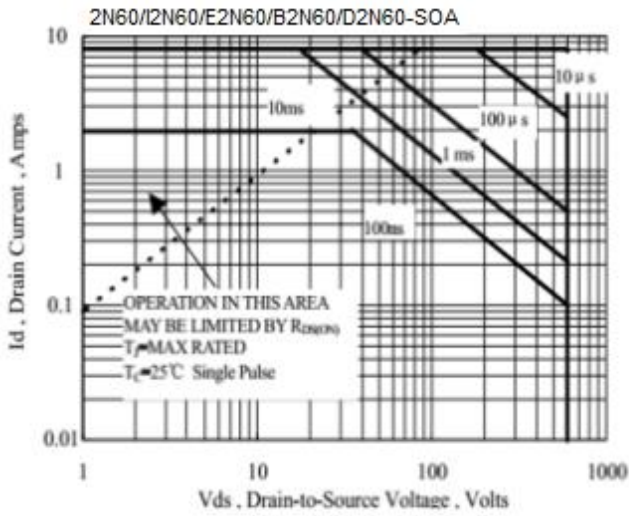


Figure 1 Maximum Forward Bias Safe Operating Area

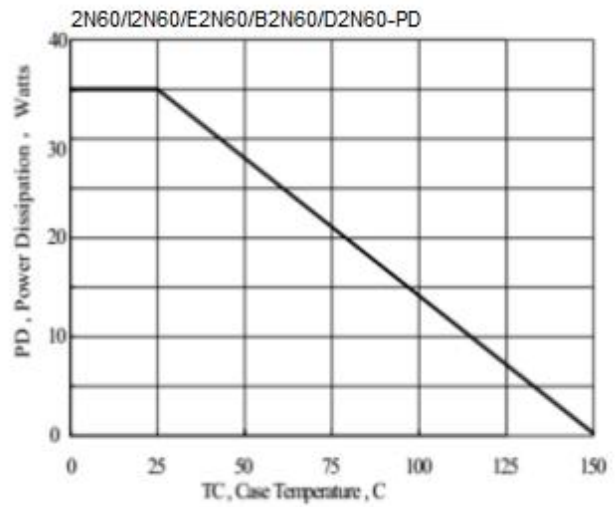


Figure 2 Maximum Power Dissipation vs Case Temperature

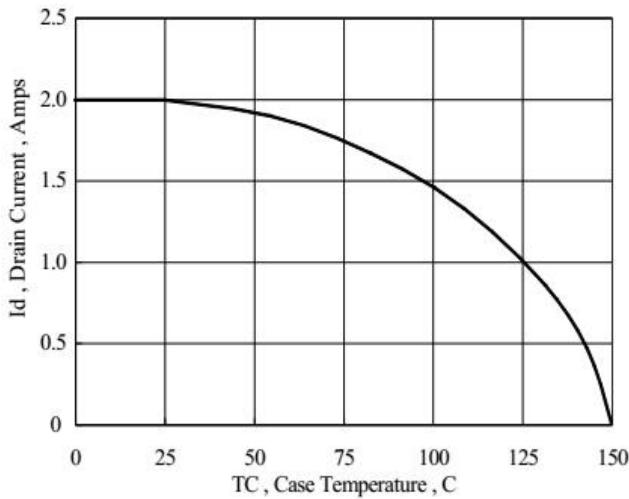


Figure 3 Maximum Continuous Drain Current vs Case Temperature

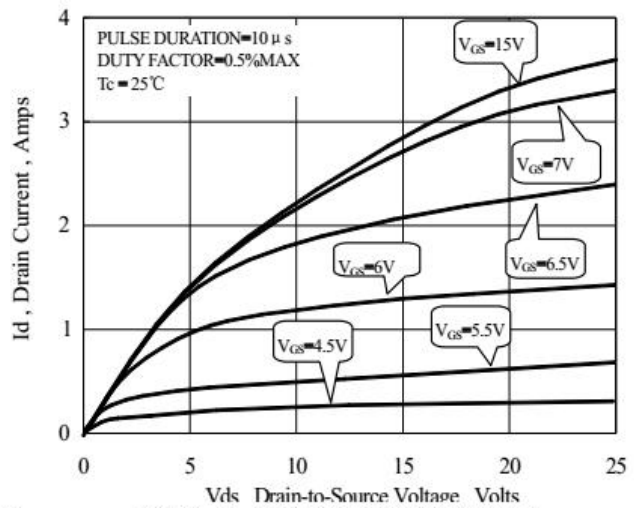


Figure 4 Typical Output Characteristics

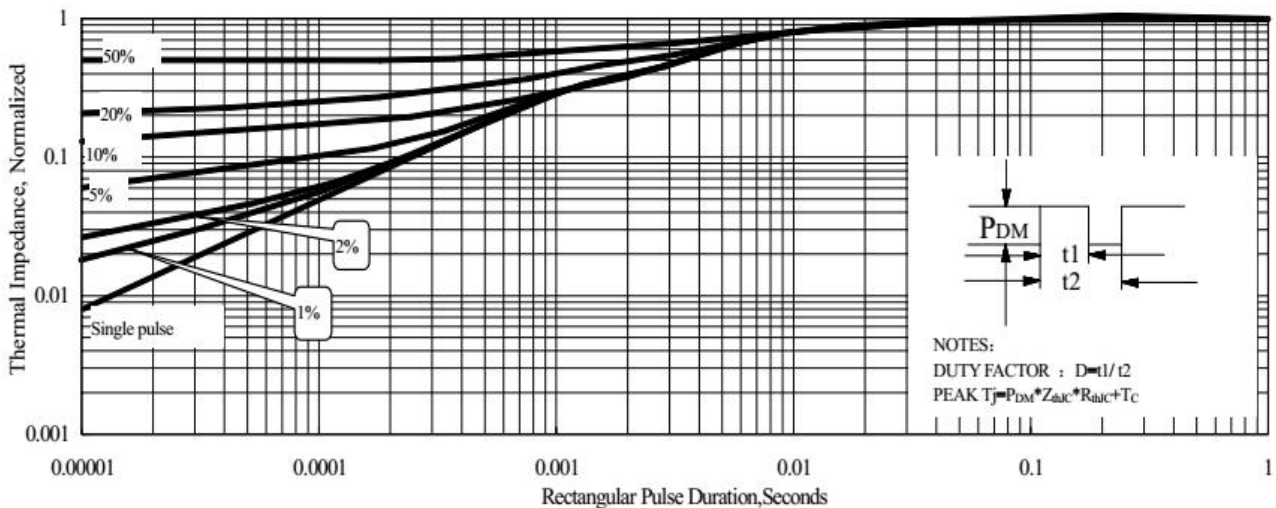


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

**5 Typical characteristics diagrams(continues)**

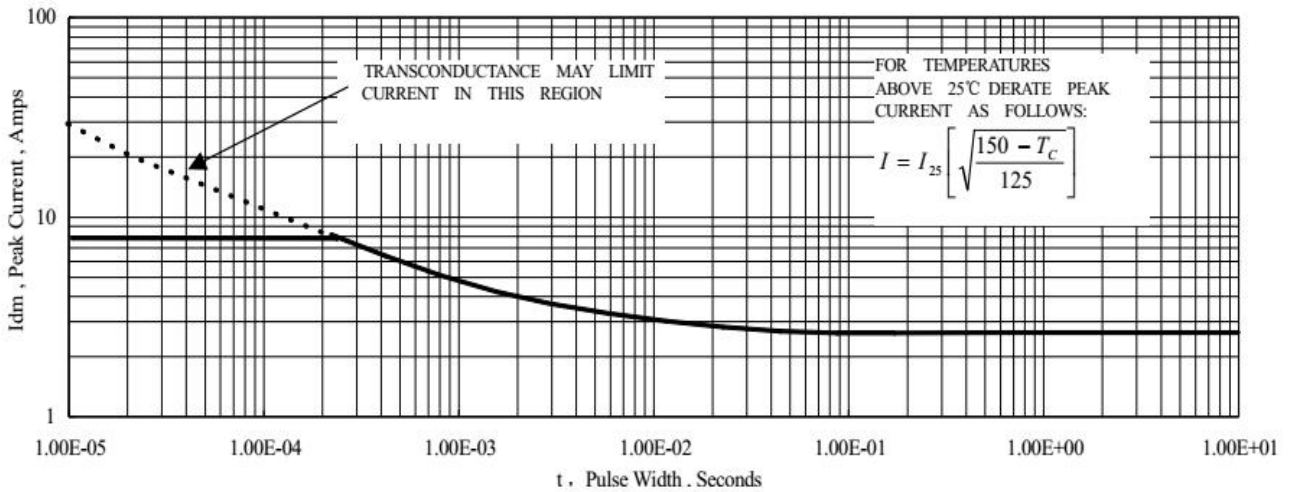


Figure 6 Maximum Peak Current Capability

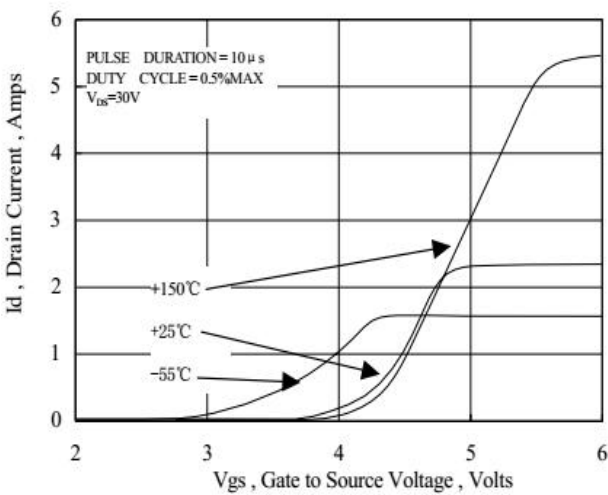


Figure 7 Typical Transfer Characteristics

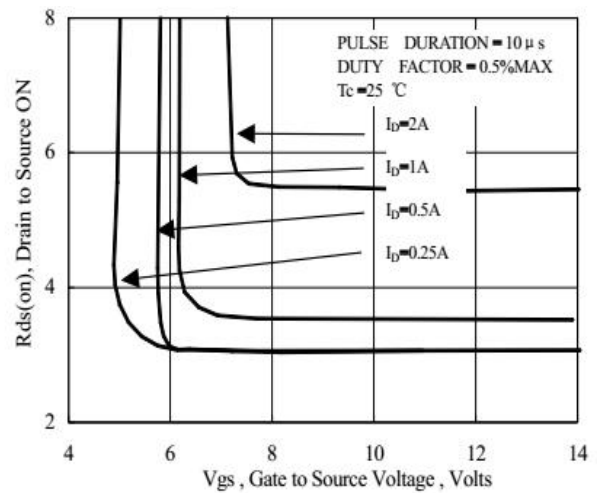


Figure 8 Typical Drain to Source ON Resistance vs Gate Voltage and Drain Current

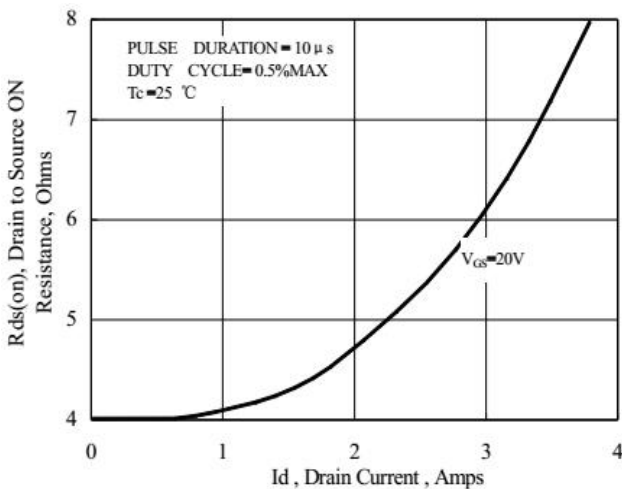


Figure 9 Typical Drain to Source ON Resistance vs Drain Current

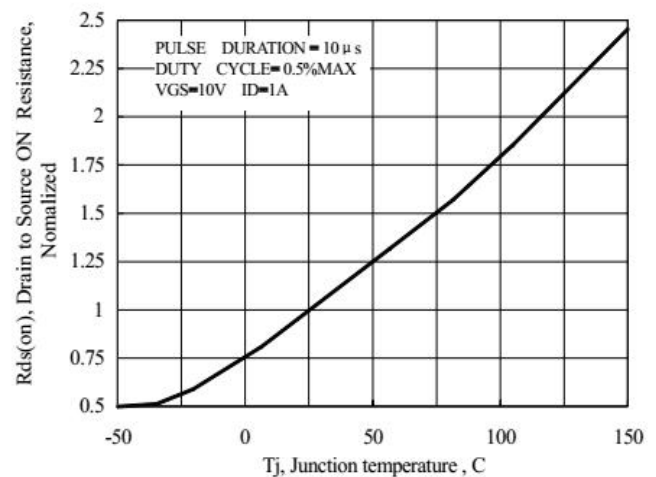


Figure 10 Typical Drain to Source on Resistance vs Junction Temperature



**5 Typical characteristics diagrams(continues)**

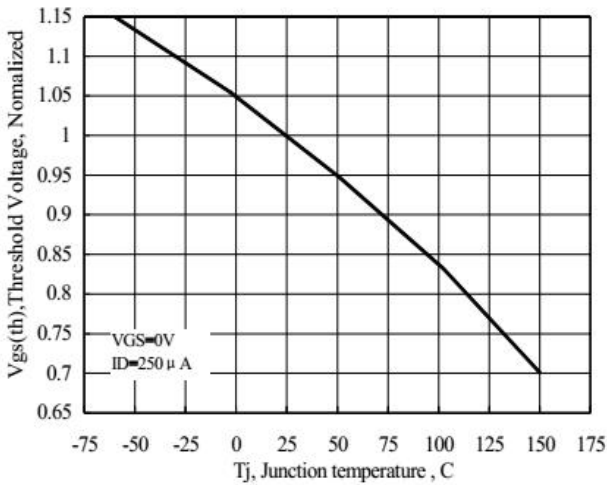


Figure 11 Typical Theshold Voltage vs Junction Temperature

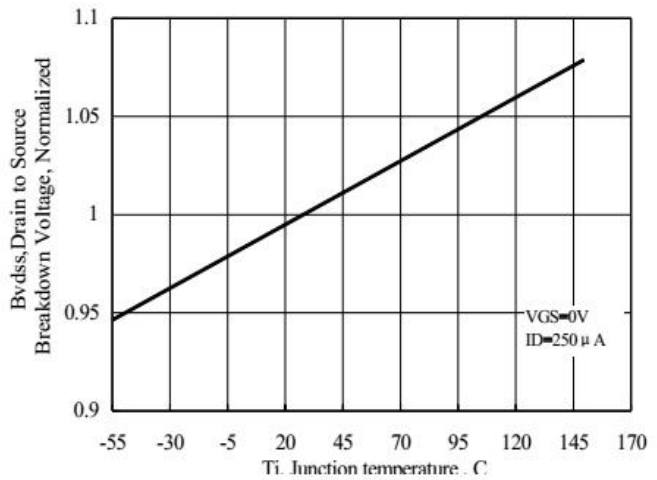


Figure 12 Typical Breakdown Voltage vs Junction Temperature

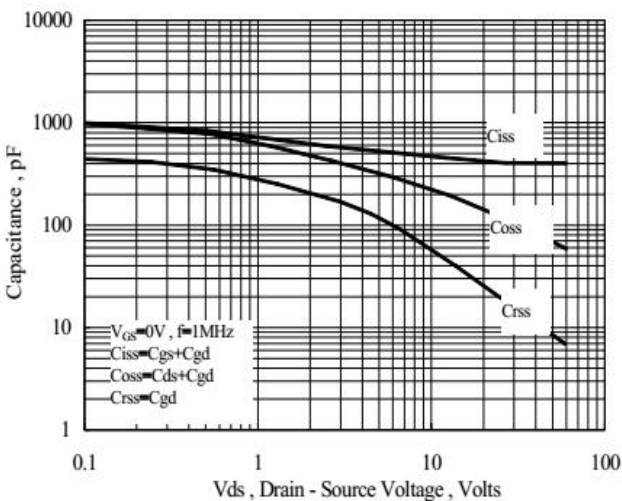


Figure 13 Typical Capacitance vs Drain to Source Voltage

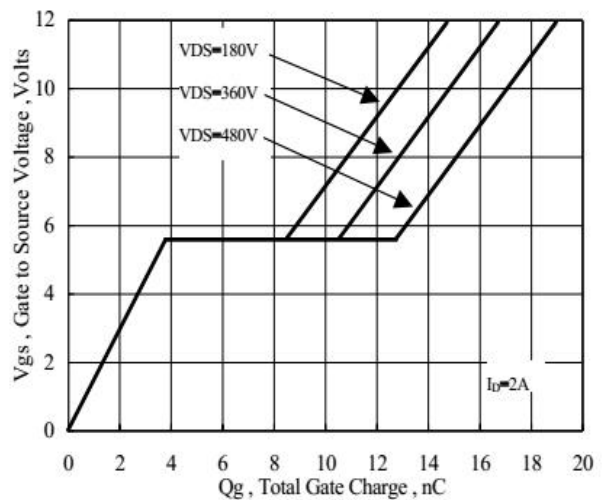


Figure 14 Typical Gate Charge vs Gate to Source Voltage

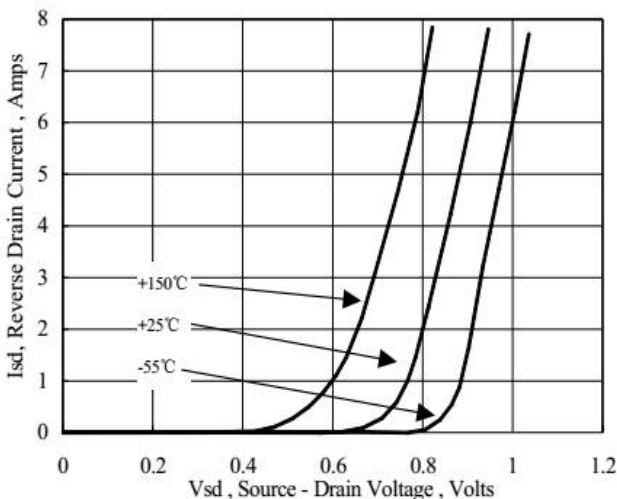


Figure 15 Typical Body Diode Transfer Characteristics

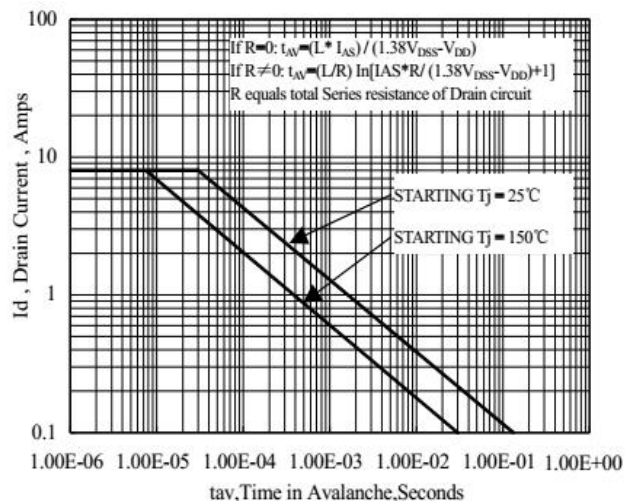


Figure 16 Unclamped Inductive Switching Capability

**5 Typical characteristics diagrams(continues)**

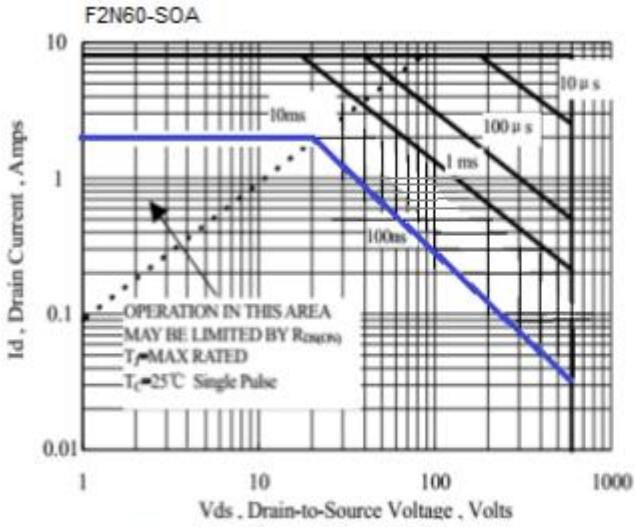


Figure 17 Maximum Forward Bias Safe Operating Area

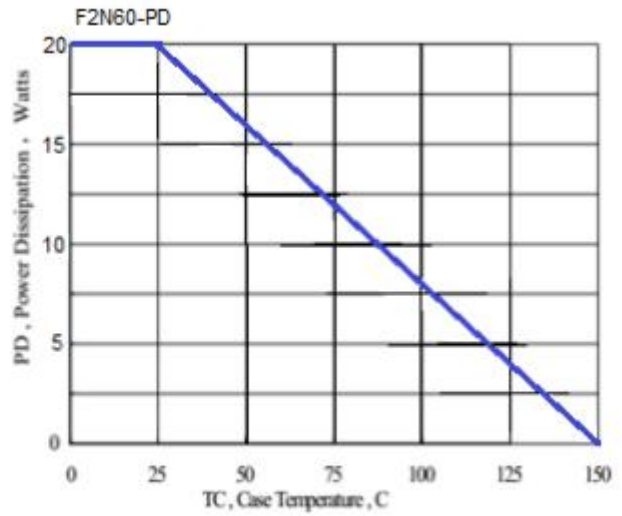


Figure 18 Maximum Power Dissipation vs Case Temperature

**6 Typical Test Circuit and Waveform**

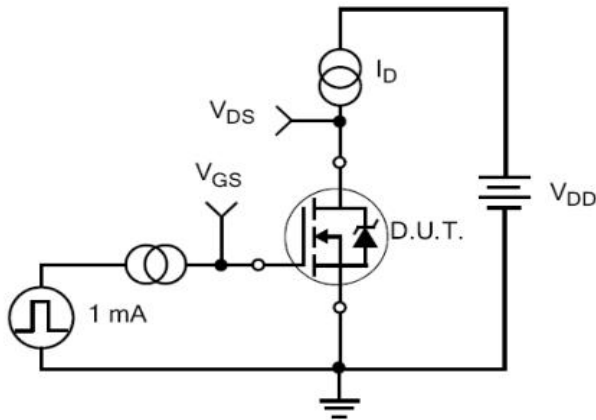


Figure 17. Gate Charge Test Circuit

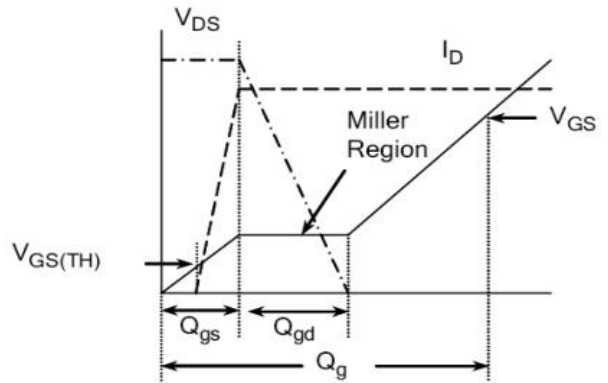


Figure 18. Gate Charge Waveform

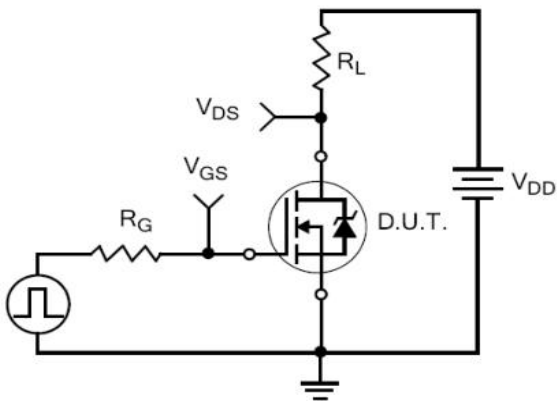


Figure 19. Resistive Switching Test Circuit

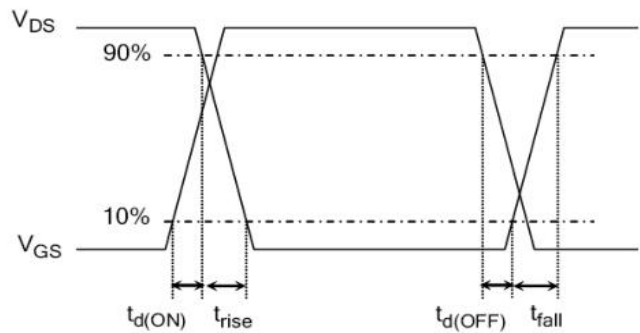


Figure 20. Resistive Switching Waveforms

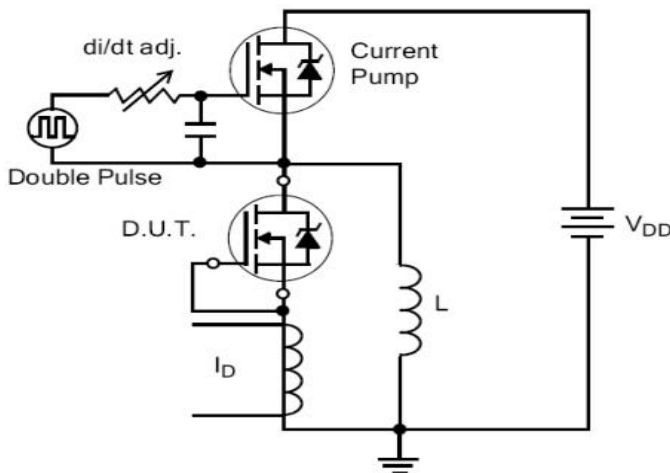


Figure 21. Diode Reverse Recovery Test Circuit

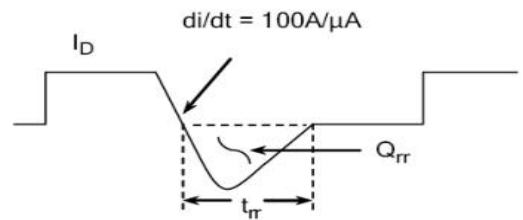


Figure 22. Diode Reverse Recovery Waveform

**6 Typical Test Circuit and Waveform(continues)**

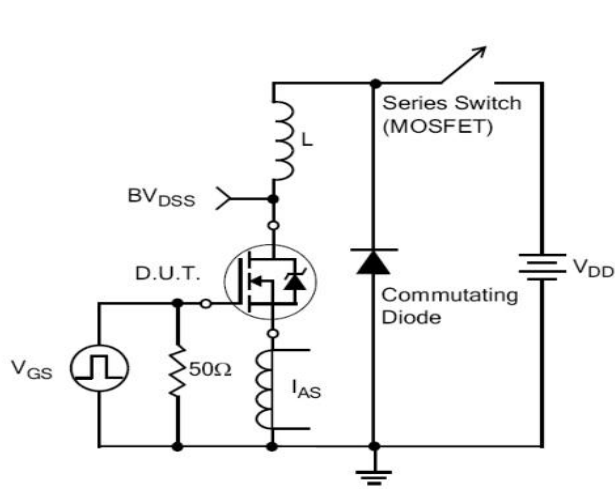


Figure 23. Unclamped Inductive Switching Test Circuit

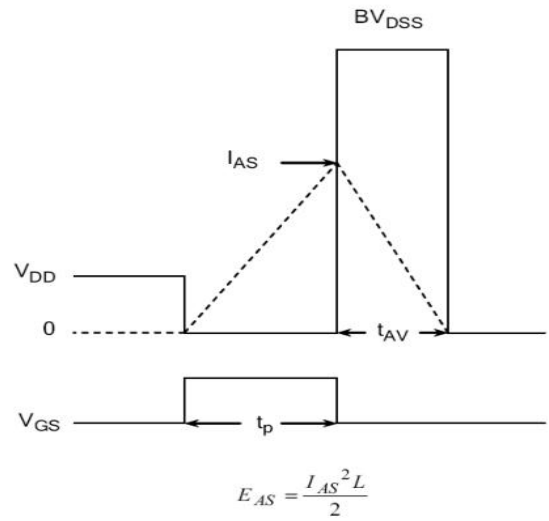
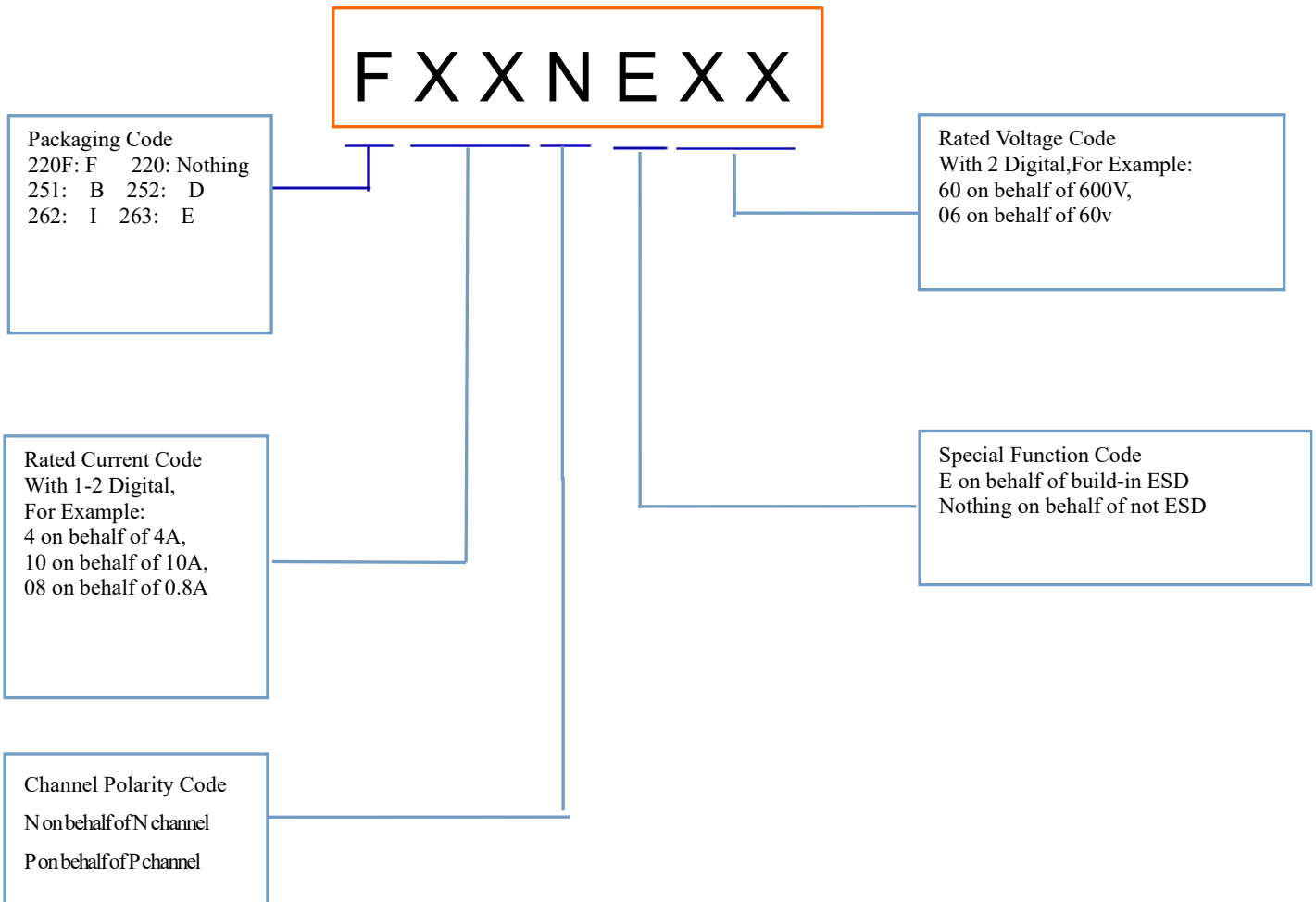


Figure 24. Unclamped Inductive Switching Waveforms

**7 Product Names Rules**



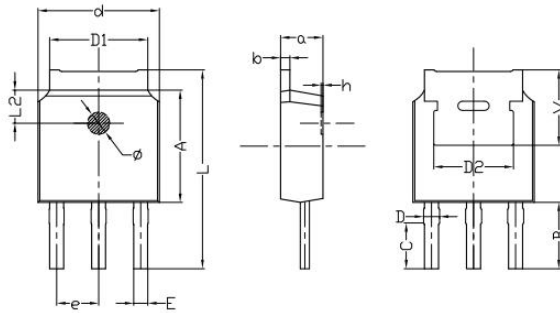


## 8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
2N60	TO-220C	2N60	Pb-free	Tube	1000/box
F2N60	TO-220F	F2N60	Pb-free	Tube	1000/box
B2N60	TO-251	B2N60	Pb-free	Tube	1000/box
D2N60	TO-252	D2N60	Pb-free	Tape & Reel	3000/box
I2N60	TO-262	I2N60	Pb-free	Tube	1000/box
E2N60	TO-263	E2N60	Pb-free	Tape & Reel	800/box

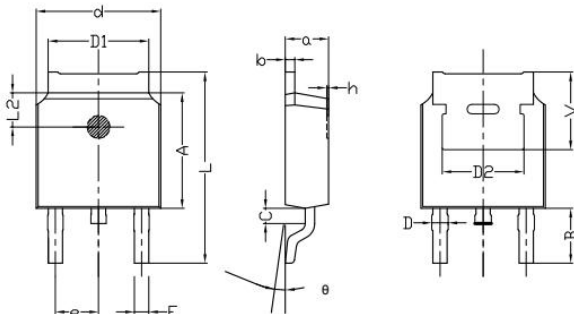
## 9 Dimensions

TO-251B PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
a	2.20	2.40	0.087	0.0946
b	0.46	0.58	0.018	0.023
c	2.45	2.65	0.097	0.104
D	0.80	0.90	0.032	0.035
d	6.30	6.70	0.248	0.264
D1	5.00	5.50	0.197	0.217
D2	TYP 4.83		TYP 0.190	
A	5.80	6.20	0.228	0.244
e	2.19	2.39	0.086	0.094
L	10.40	11.00	0.4098	0.4334
B	3.50	3.70	0.1379	0.1458
L2	1.5	1.8	0.059	0.071
φ	1.10	1.30	0.0433	0.0512
h	0.00	0.30	0.000	0.012
V	5.25	5.85	0.207	0.230
E	0.60	0.80	0.0236	0.0315

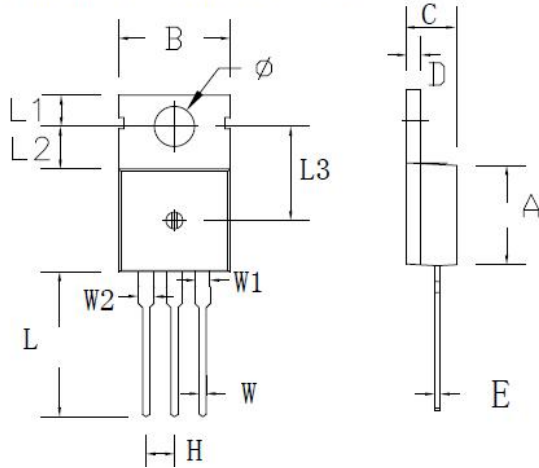
TO-252B PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
a	2.20	2.40	0.087	0.095
b	0.46	0.58	0.018	0.023
c	0.70	0.90	0.028	0.035
D	0.80	1.00	0.032	0.039
d	6.30	6.70	0.248	0.264
D1	5.00	5.50	0.197	0.217
D2	TYP 4.83		TYP 0.190	
A	5.80	6.20	0.228	0.244
e	2.19	2.39	0.086	0.094
L	9.40	10.40	0.370	0.409
B	2.6	3.2	0.102	0.126
L2	1.5	1.8	0.059	0.071
θ	0	8	0	8
h	0	0.3	0	0.012
V	5.25	5.85	0.207	0.230

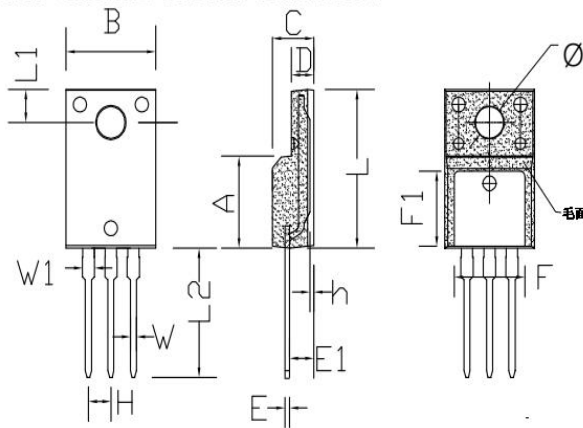
9 Dimensions(continues)

TO-220C PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
H	2.54 TYP		0.100 TYP	
W	0.60	0.95	0.024	0.037
W1	1.05	1.45	0.041	0.057
W2	1.20	1.60	0.047	0.063
L	12.60	13.40	0.496	0.528
L1	2.45	2.95	0.096	0.116
L2	3.45	3.95	0.136	0.156
L3	8.15	8.65	0.321	0.341
phi	3.50	3.90	0.138	0.154

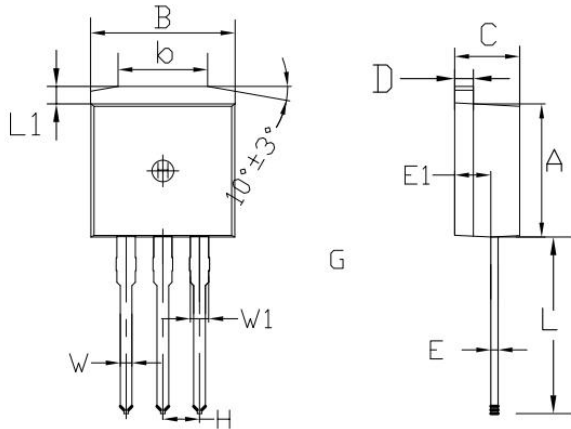
TO-220F PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	10.00	10.50	0.394	0.413
C	4.30	4.90	0.169	0.193
D	2.30	2.70	0.091	0.106
L	15.55	16.15	0.612	0.636
h	0.40	0.60	0.016	0.024
L1	3.15	3.55	0.124	0.140
L2	12.65	13.35	0.498	0.526
W	0.70	0.90	0.028	0.035
W1	1.15	1.55	0.045	0.061
H	2.54 TYP		0.100 TYP	
E	0.48	0.53	0.019	0.021
phi	2.90	3.40	0.114	0.134
E1	2.40	2.90	0.094	0.114
F	7.75	8.25	0.305	0.325
F1	7.35	7.85	0.289	0.309

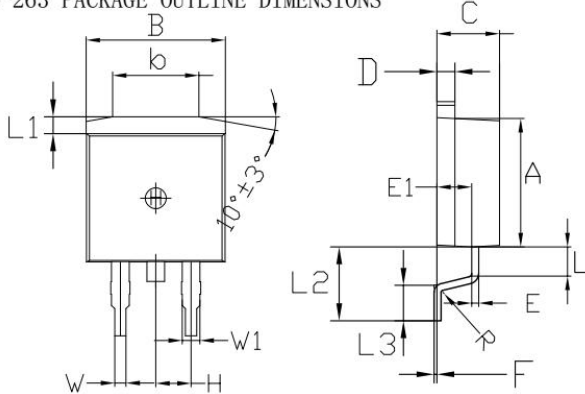
9 Dimensions(continues)

TO-262 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
L	12.25	13.75	0.482	0.541
L1	1.15	1.45	0.045	0.057
E1	2.4	2.6	0.0945	0.1024
W	0.80	0.82	0.0315	0.034
W1	1.20	1.30	0.047	0.051
H	2.54 TYP		0.200 TYP	
b	5.50	6.50	0.216	0.256

TO-263 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
L	1.90	2.30	0.075	0.091
L1	1.15	1.45	0.045	0.057
R	0.24	0.26	0.0095	0.0102
W	0.80	0.82	0.0315	0.0323
W1	1.20	1.30	0.047	0.051
H	2.54 TYP		0.200 TYP	
b	5.50	6.50	0.216	0.256
E1	2.4	2.6	0.0946	0.1024
L2	5.20	5.80	0.205	0.228
L3	2.20	3.20	0.087	0.126
F	0.03	0.23	0.0012	0.0091

## 10 Attentions

- ROUM Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Roma products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

## 11 Appendix

Revision history:

Date	REV.	Description	Page
2017.03.14	1.0	Original	